

IN THE CLAIMS:

1-14. (Cancelled)

15. (New) A semiconductor device, comprising:
an embedded insulation layer formed in a semiconductor substrate;
a plurality of power semiconductor elements formed on said semiconductor substrate;
a trench isolating between said plurality of power semiconductor elements formed on said semiconductor substrate on said embedded insulation layer;
an isolator insulating and driving control electrodes of said power semiconductor elements; and
wherein said plurality of power semiconductor elements are each connected to at least two different device terminals in order to provide connectability to said semiconductor device.

16. (New) A semiconductor device according to claim 15, wherein said plurality of power semiconductor elements drive an ignition coil.

17. (New) A semiconductor device according to claim 15, wherein said plurality of power semiconductor elements drive a fuel injection valve.

18. (New) A semiconductor device according to claim 15, wherein said plurality of power semiconductor elements have an input control circuit

supplying a control signal of a specific control pattern to said control electrodes of
said plurality of power semiconductor elements on the base of input signals.